

BUK9Y19-100E

N-channel 100 V, 19 m Ω logic level MOSFET in LFPAK56 Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

Applications 2.

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

Quick reference data 3.

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	56	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	167	W
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	14.6	19	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	14.1	-	nC



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4. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	[d	G T T
4	G	gate	و و و و و	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

5. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y19-100E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

6. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y19-100E	91910E

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	100	V
V_{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	167	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	56	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	40	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	226	Α

BUK9Y19-100E

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Symbol	Parameter	Conditions		Min	Max	Unit	
T _{stg}	storage temperature			-55	175	°C	
T _j	junction temperature			-55	175	°C	
Source-drain	Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	56	Α	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$		-	226	Α	
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 56 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	94.1	mJ	

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

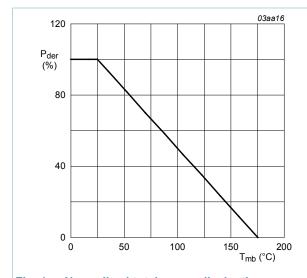


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

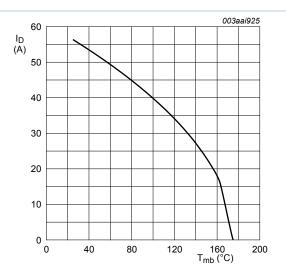


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

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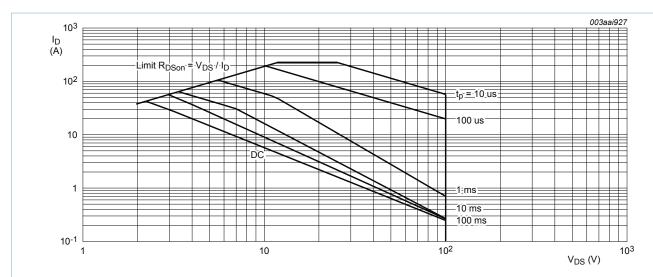
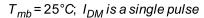


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



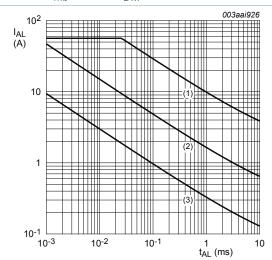


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

8. Thermal characteristics

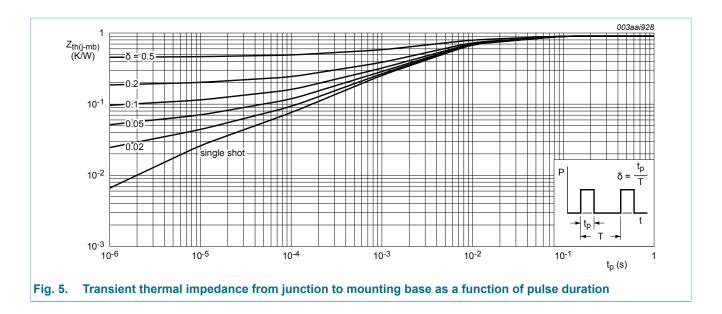
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.9	K/W

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N-channel 100 V, 19 m Ω logic level MOSFET in LFPAK56



9. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	100	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.04	10	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	14.6	19	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	14	18	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	52.4	mΩ
Dynamic ch	naracteristics		1			
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	39	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	8.5	-	nC
Q _{GD}	gate-drain charge		-	14.1	-	nC

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 15}}$		-	3814	5085	pF
C _{oss}	output capacitance			-	222	266	pF
C _{rss}	reverse transfer capacitance			-	133	182	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_{L} = 5 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C		-	18.5	-	ns
t _r	rise time			-	36.8	-	ns
t _{d(off)}	turn-off delay time			-	59.6	-	ns
t _f	fall time			-	34.3	-	ns
Source-dra	ain diode		l				
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	8.0	1.2	V
t _{rr}	reverse recovery time	I_S = 15 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C		-	38	-	ns
Q _r	recovered charge			-	56	-	nC

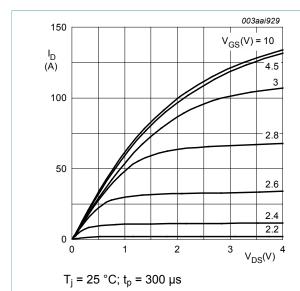


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

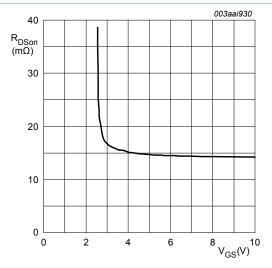


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 15A$

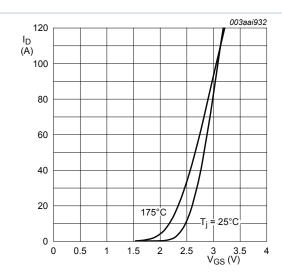


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

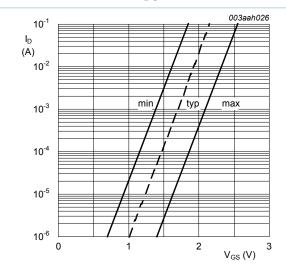


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

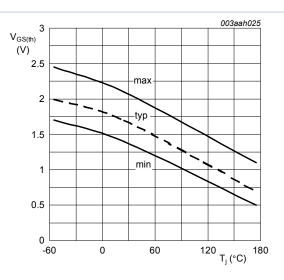
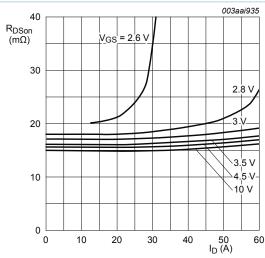


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}



 $T_j = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

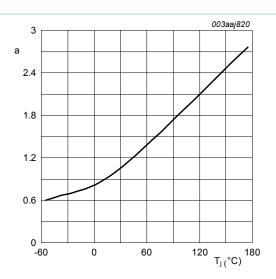


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

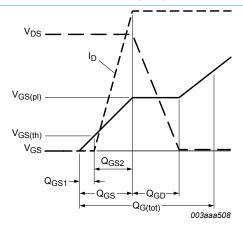


Fig. 14. Gate charge waveform definitions

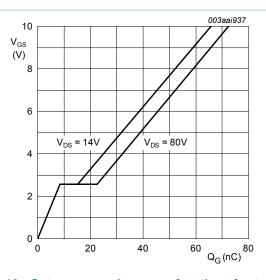


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 15A$$

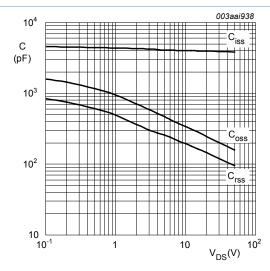


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
; $f = 1MHz$

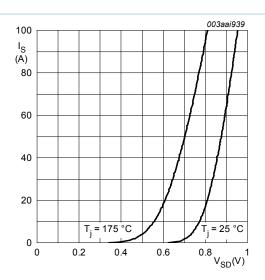
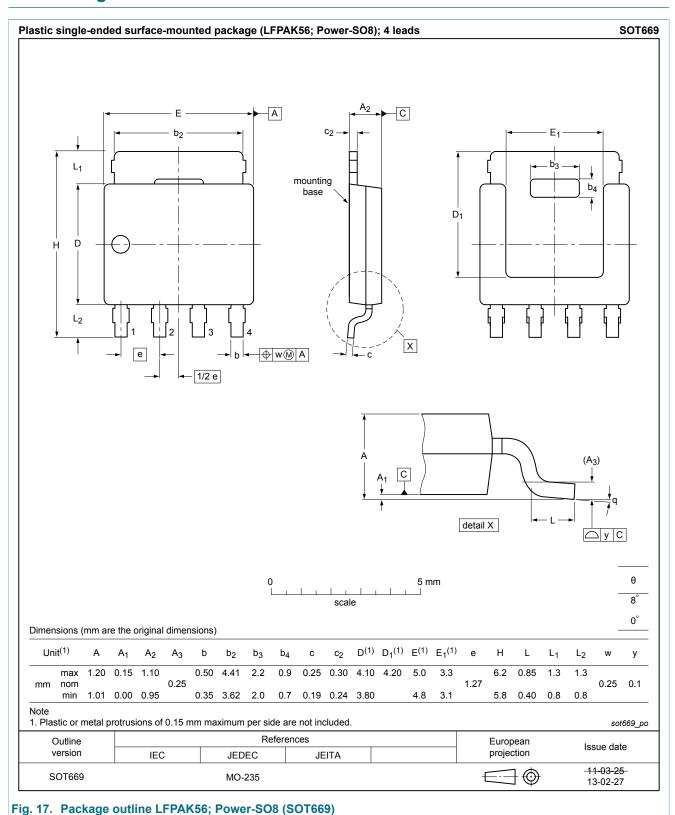


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values $V_{\rm GS} = 0V$

10. Package outline



BUK9Y19-100E

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N-channel 100 V, 19 m Ω logic level MOSFET in LFPAK56

12. Contents

1	General description	1
2	Applications	1
3	Quick reference data	1
4	Pinning information	2
5	Ordering information	
6	Marking	
7	Limiting values	
8	Thermal characteristics	
9	Characteristics	5
10	Package outline	10
11	Legal information	
11.1	Data sheet status	11
11.2	Definitions	11
11.3	Disclaimers	11
11.4	Trademarks	

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